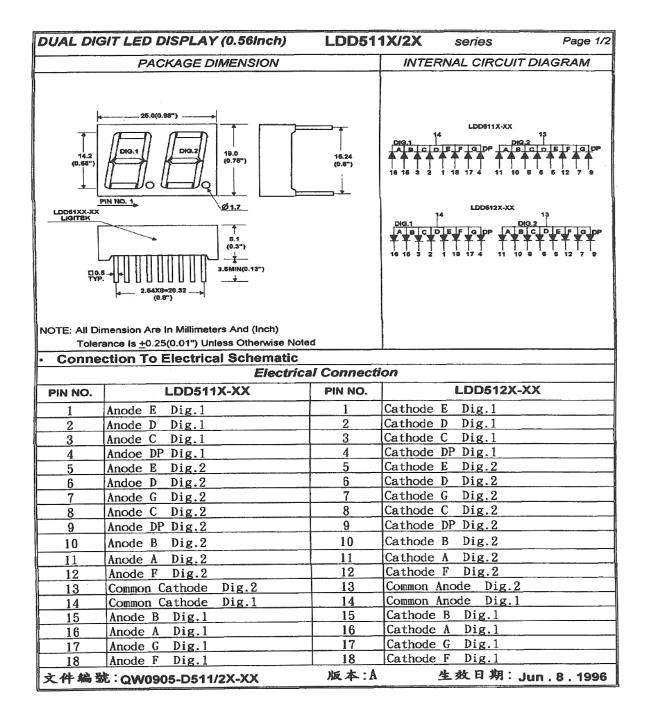
Jameco Part Number 24715



Common Cathode	DOUBLE D		LDD51						series		Page 2/2						
PART NO CHIP Cethode or ande Cmm	· Part Sele	ection And A	\ppli	cati	on In	form	atio	n (Ratir	ngs	At 2	5°C A	mbie	nt)			
PART NO							λР		Δλ	L		E	lectric	al			
Min Typ, Mex Min Typ, Min Typ, Mex Min Typ,	PART NO	CHII	HIP				(nm)		(nm)		Vf(v)			lv(m		IV-M	
LDD5111-XX GaP Red Carthode S65 30 1.7 2.1 2.8 0.5 0.8 2:1		material	erial emitted								Min	Typ,	Max	Min	Тур.		
Common	LDD5115-XX	GaAlAs	Re	Red				0	20)	1.5	1.7	2.4	1.9	3.1	2:1	
Cathode Green Cathode Section Cathode Section Secti	LDD5111-XX	DD5111-XX GaP		Red				7	90		1.7	2.1	2.8	0.5	0.8	2:1	
LDD5114-XX GaASP/GaP Orange	LDD5112-XX	12-XX GaP		Green				565		30		2.1	2.8	1.4	2.4	2:1	
LDD5125-XX GaAlAs Red LDD5121-XX GaP Red LDD5122-XX GaP Green CDD5122-XX GaP Green CDD5122-XX GaAsP/GaP Yellow LDD5122-XX GaAsP/GaP Yellow CDD5123-XX GaAsP/GaP Yellow CDD5124-XX GaAsP/GaP Yellow CDD5124-XX GaAsP/GaP Orenge CDD5124-XX Orenge CDD5	LDD5113-XX	13-XX GaAsP/GaP		Yellow				585		35		2.0	2.8	1.3	2.2	2:1	
Common Anode G97 90 1.7 2.1 2.8 0.5 0.8 2:1	LDD5114-XX	GaAsP/GaP	Orange				63	5	45	5	1.7	2.0	2.8	1.4	2.4	2:1	
LDD5122-XX GaP Green Anode 565 30 1.7 2.1 2.8 1.4 2.4 2:1	LDD5125-XX	GaAlAs	AIAs Re				660		20		1.5	1.7	2.4	1.9	3.1	2:1	
LDD5122-XX GaP Green Anode 565 30 1.7 2.1 2.8 1.4 2.4 2:1	LDD5121-XX	GaP	Red		Common		69	7	90		1.7	2.1	2.8	0.5	0.8	2:1	
Companies Com	LDD5122-XX	GaP	Green				56	5	30)	1.7	2.1	2.8	1.4	2.4	2:1	
- Absolute Maximum Rating (Ta=25°C) Parameter Red Gre- Yellow Oralge Unit Remark	LDD5123-XX	GaAsP/GaP	Yell	low		58	5	35		1.7	2.0	2.8	1.3	2.2	2:1		
Parameter			Orange					35	45		1.7	2.0	2.8	1.4	2.4	2:1	
Forward Current Per Chip SR H G Y E	 Absolute 	Maximum Ra	iting	(Ta	=25°C)											
Heak Current Per Chip (Duty 1/10, 0.1MS Pulse Width) 200 60 120 80 120 mA 120 mA 1/10, 0.1MS Pulse Width) 110 45 100 85 100 mW 1/10 10 10 10 mA 1/10 10 10 mA 1/10 10 10 mA 1/10 10 mA 1/10 10 mA 1/10 10 10 mA 1/10 10 mA 1/10 10 10 mA 1/10	Parameter		Red		ı	Gree			Yellow		Orange		Unit		Remark		
Peak Current Per Chip (Duty 1/10, 0.1MS Pulse Width) 200	Forward Current Per Chip		SR		Н		G		Y			E	1				
1/10, 0.1MS Pulse Width) 20 0 45 100 85 100 mW Derating Linear From 25°C Per Chip 0.45 0.25 0.45 0.45 0.45 mA/ °C Reverse Current Per Any Chip 10 10 10 10 μA Operating Temperature -25°C T0 +85°C -25°C T0 +85°C Storage Temperature -25°C T0 +85°C Solder Temperature 1/16 Inch Below Seating Plane For 3 Seconds At 260°C • Test Condition For Each Parameter Parameter Symbol Unit Test Condition Forward Voltage Per Chip Vf volt If=20mA Luminous Intensity Per Chip Iv mcd If=10mA Peak Emission Wavelength λP nm If=20mA Spectral Line Half-Width Δλ nm If=20mA Reverse Current Any Chip Ir μA Vr=5V			40		15		30		20			30	n	mA			
Power Dissipation Per Chip 110 45 100 85 100 mW	, , ,		200		60		120		80			120	n	nA			
Chip Reverse Current Per Any Chip 10 10 10 10 μΑ Operating Temperature -25°C TO +85°C -25°			110		45	100			85		100		mW				
Operating Temperature	1		0.45		0.25	0.45		0.45			0.45		mA/ °C				
Storage Temperature	Reverse Current Per Any Chip			10			10		10		10		μА				
Storage Temperature	Operating Tem	perature					-2	5ºC	T0 +	85°C							
Solder Temperature 1/16 Inch Below Seating Plane For 3 Seconds At 260°C Test Condition For Each Parameter Parameter Symbol Unit Test Condition Forward Voltage Per Chip Vf volt If=20mA Luminous Intensity Per Chip Iv mcd If=10mA Peak Emission Wavelength λ p nm If=20mA Spectral Line Half-Width Δλ nm If=20mA Reverse Current Any Chip Ir μ A Vr=5V	95°C TO 195°C																
Parameter Symbol Unit Test Condition Forward Voltage Per Chip Vf volt If=20mA Luminous Intensity Per Chip Iv mcd If=10mA Peak Emission Wavelength λP nm If=20mA Spectral Line Half-Width Δλ nm If=20mA Reverse Current Any Chip Ir μA Vr=5V	Solder Temper	ature 1/16 Inch E	elow S	Seati	ng Plan	e For 3	Seco	nds	At 260	°C							
Forward Voltage Per Chip Vf volt If=20mA	 Test Cor 	dition For Ea	ch P	arar	neter												
Luminous Intensity Per Chip Iv mcd If=10mA Peak Emission Wavelength λP nm If=20mA Spectral Line Half-Width Δλ nm If=20mA Reverse Current Any Chip Ir μA Vr=5V	Parameter						Symbol				Unit			Test Condition			
Peak Emission Wavelength λP nm If=20mA Spectral Line Half-Width Δλ nm If=20mA Reverse Current Any Chip Ir μA Vr=5V	Forward Volt	age Per Chip					Vf				volt			If=20mA			
Peak Emission Wavelength λP nm If=20mA Spectral Line Half-Width Δλ nm If=20mA Reverse Current Any Chip Ir μA Vr=5V							Iv			mcd							
Reverse Current Any Chip Ir µA Vr=5V							λР			nm			lf=20mA				
Reverse Current Any Only	Spectral Line	Half-Width					Δλ				nm			If=20mA			
Luminous Intensity Matching Ratio IV-M	Reverse Cur	rent Any Chip					Ir				μА			Vr=5V			
and the state of t	Luminous Int	ensity Matching	Ratio				T	IV-	М								